CNB2001

Reflective photosensor

Non-contact point SW, object sensing

Overview

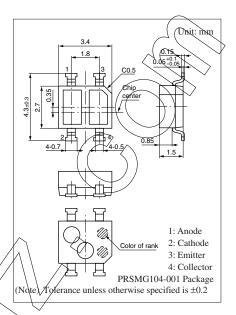
CNB2001 is a small, thin SMD-compatible reflective photosensor consisting of a high efficiency GaAs infrared light emitting diode which is integrated with a high sensitivity Darlington phototransistor in a single resin package.

■ Features

- Reflow-compatible reflective photosensor
- Ultraminiature, thin type: 2.7 mm × 3.4 mm (height: 1.5 mm)
- Visible light cutoff resin is used
- High current-transfer ratio

■ Absolute Maximum Ratings $T_a = 25$ °C

	Symbol	Rating	Unit	
Input (Light	Reverse voltage	V _R	6	(V)
emitting diode)	Forward current	I_F	50	mA
	Power dissipation *1	P_{D}	75	mW
Output (Photo	Collector-emitter voltage	V _{CEO}	35	v (
transistor)	(Base open)			
	Emitter-collector voltage	V _{ECO}	6	/v
	(Base open)			
	Collector current	I_C	30 </td <td>mA</td>	mA
	Collector power dissipation *2	P _C	75	mW
Temperature	Operating ambient temperature	Topr	-25 to +85	\ °C
	Storage temperature	T _{stg}	+40 to +100	°C



Note) *1: Input power derating ratio is $1.0 \text{ mW/}^{\circ}\text{C}$ at $T_a \ge 25^{\circ}\text{C}$.

*2: Output power derating ratio is $1.0 \text{ mW/}^{\circ}\text{C}$ at $T_a \ge 25^{\circ}\text{C}$.

■ Electrical-Optical Characteristics T_a = 25°C ± 3°C

	Parameter 4	Symbol	Conditions	Min	Тур	Max	Unit
Input	Forward voltage	$V_{\rm F}$	$T_F = 20 \text{ mA}$		1.2	1.4	V
characteristics	Reverse current	I_R	$V_R = 3 \text{ V}$			10	μΑ
Output	Collector-emitter cutoff current	I_{CEO}	$V_{CE} = 10 \text{ V}$			1.0	μΑ
characteristics	()						
Transfer	Collector current *1,3	$\sqrt{I_{\rm C}}$	$V_{CC} = 2 \text{ V}, I_F = 4 \text{ mA}, R_L = 100 \Omega, d = 1 \text{ mm}$	0.52		15.00	mA
characteristics	Dark current	I_D	$V_{CC} = 2 \text{ V}, I_F = 4 \text{ mA}, R_L = 100 \Omega$			5.0	μΑ
	Collector-emitter saturation voltage	V _{CE(sat)}	$I_F = 4 \text{ mA}, I_C = 0.5 \text{ mA}$			1.2	V
	Rise time *2	t _r	$V_{CC} = 2 \text{ V}, I_{C} = 10 \text{ mA}$		120		μs
	Fall time *2	t _f	$R_L = 100 \Omega$		115		μs

*2: Switching time

Note) 1. Input and output are handled electrically.

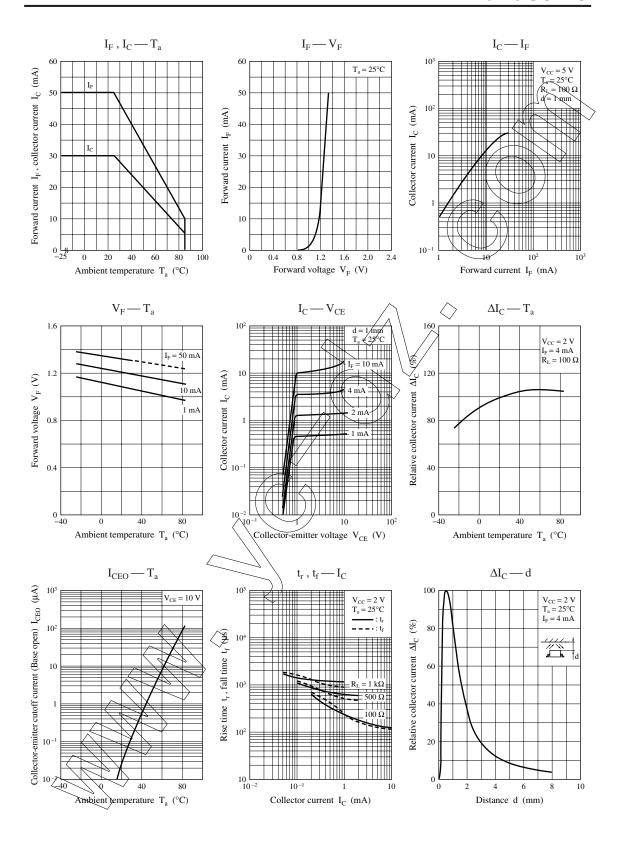
3. *1: Output surrent measurement

2. This product is not designed to withstand radiation

or an outside dance measurement	2. 5 Wittening time		
method	measurement circuit		
Glass plate	Glass plate t.: Rise time		
Evaporated Al	Evaporated Al t _c : Fall time		
d = 1 mm	d = 1 mm Sig. in		
$I_{F} = \begin{bmatrix} I_{C} & I_$	Sig. out 90%		

*3: Rank classification

Rank	Q	R	S
I_{C} (mA)	0.52 to 1.94	1.45 to 5.40	4.00 to 15.00
Color	Orange	White	Light blue



Caution for Safety

⚠ DANGER

■ This product contains Gallium Arsenide (GaAs).

GaAs powder and vapor are hazardous to human health if inhaled or ingested. Do not burn, destroy, cut, cleave off, or chemically dissolve the product. Follow related laws and ordinances for disposal. The product should be excluded form general industrial waste or household garbage.

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